





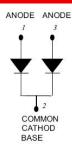
225CNQ015 SCHOTTKY RECTIFIER



Features

- 125°C T_J operation
- · Center tap module
- High purity, high temperature epoxy encapsulation for
- enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Base plate: Nickel plated; Terminals: Nickel plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- High current switching power supply
- Plating power supply
- Free-Wheeling diodes
- Reverse battery protection
- Converters
- UPS System
- Welding

Maximum Ratings(limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	15	V
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _C =74°C,	110(Per Leg)	Α
Average Nectified Forward Current		rectangular wave form	220(Per Device)	7 /
Peak One Cycle Non-Repetitive Surge Current (Per Leg)	I _{FSM}	8.3 ms, half Sine pulse	2040	Α
Non-Repetitive Avalanche Energy(Peg Leg)	E _{AS}	T _J =25℃,I _{AS} =2A,L=4.5mH	9	mJ
Repetitive Avalanche Current(Peg Leg)	lar	Current decaying linearly to zero in 1 µsec Frequency limited by T _J max. V _A =1.5×V _R typical	2	A

- China Germany Korea Singapore United States
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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V _{F1}	@ 110A, Pulse, T _J = 25 °C @ 220A, Pulse, T _J = 25 °C	0.36 0.48	0.38 0.49	V
	V _{F2}	@ 110A, Pulse, T _J = 125 °C @ 220A, Pulse, T _J = 125 °C	0.30 0.37	0.32 0.42	V
Reverse Current(Per Leg)*	I _{R1}	$@V_R = \text{rated } V_{R,} T_J = 25 ^{\circ}\text{C}$	11	40	mA
	I _{R2}	$@V_R = \text{rated } V_{R}, T_J = 125 ^{\circ}\text{C}$	330	2000	mA
	I _{R3}	@V _R =12V _, T _J = 100 °C	295	1780	mA
	I _{R4}	@V _R = 5V, T _J = 100 °C	220	1080	mA
Junction Capacitance(Per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	6650	7700	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specific	cation	Units
Junction Temperature	TJ	-	-55 to	+125	°C
Storage Temperature	T _{stg}	-	-55 to +125		°C
Typical Thermal Resistance Junction to Case(Per leg)	R₀Jc	DC operation	0.4	0	°C/W
Typical Thermal Resistance Junction to Case(Per package)	$R_{ heta JC}$	DC operation	0.20		°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.08		°C/W
Mounting Torque	т		Mounting Torque	24(min) 35(max)	Va om
Mounting Torque	T_M	-	Terminal Torque	35(min) 46(max)	- Kg-cm
Approximate Weight	wt	-	91		g

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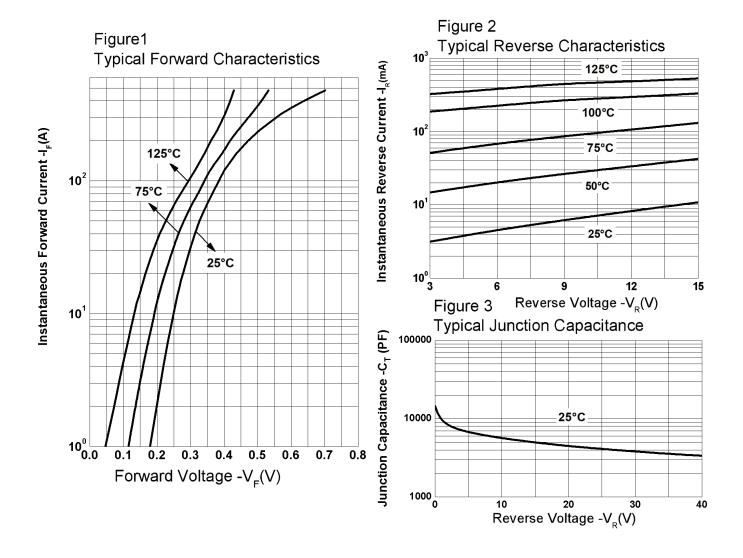
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Ratings and Characteristics Curves



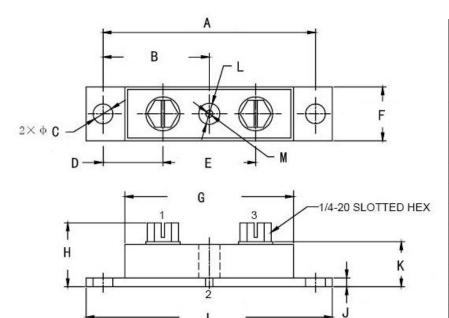
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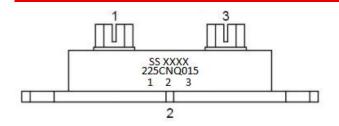


Mechanical Dimensions PRM4 Non-Isolated (Millimeters/Inches)



SYMBOL	Millimeters		Inches		
STIVIBUL	Min.	Max.	Min.	Max.	
Α	78.74	81.28	3.100	3.200	
В	37.47	42.55	1.475	1.675	
С	6.89	7.69	0.271	0.303	
D	19.51	24.59	0.768	0.968	
E	33.02	38.10	1.300	1.500	
F	17.78	20.32	0.700	0.800	
G	60.96	64.77	2.400	2.550	
Н	17.26	23.25	0.680	0.915	
I	90.17	92.71	3.550	3.650	
J	3.02	3.68	0.119	0.145	
K	14.30	16.15	0.563	0.636	
L	9.27	10.79	0.365	0.425	
М	4.37	5.28	0.172	0.208	

Marking Diagram



Ordering Information

Device	Package	Shipping	
225CNQ015	PRM4(Non- Isolated) (Pb-Free)	9 pcs/box	

Where XXXX is YYWW

225CNQ015 = Part name SS = SS YY = Year WW = Week

Cautions: Molding resin

Epoxy resin UL:94V-0









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